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## P-Channel NexFET™ Power MOSFET

Check for Samples: CSD25301W1015

#### **FEATURES**

- Ultra Low Qg and Qgd
- Small Footprint
- Low Profile 0.62mm Height
- Pb Free
- RoHS Compliant
- Halogen Free
- CSP 1 x 1.5 mm Wafer Level Package

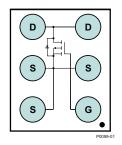
## **APPLICATIONS**

- Battery Management
- Load Switch
- Battery Protection

## **DESCRIPTION**

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile.

**Top View** 



## R<sub>DS(ON)</sub> vs V<sub>GS</sub> 300 $R_{DS(on)}$ – On-State Resistance – $m\Omega$ $I_D = -1A$ 250 200 T<sub>C</sub> = 125°C 150 100 50 $T_C = 25^{\circ}C$ 0 0 6 -V<sub>GS</sub> - Gate to Source Voltage - V G006

#### PRODUCT SUMMARY

$V_{DS}$	Drain to Source Voltage	-20		V
$Q_g$	Gate Charge Total (4.5V)	1.9		nC
$Q_{gd}$	Gate Charge Gate to Drain	0.4		nC
		$V_{GS} = -1.5V$	-1.5V 175	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = -2.5V$	80	mΩ
		$V_{GS} = -4.5V$	62	mΩ
V <sub>GS(th)</sub>	Voltage Threshold	-0.75		V

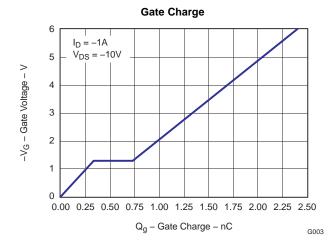
#### ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD25301W1015	1 x 1.5 Wafer Level Package	7-inch reel	3000	Tape and Reel

#### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	-20 \	
$V_{GS}$	Gate to Source Voltage	±8	V
I <sub>D</sub>	Continuous Drain Current, T <sub>C</sub> = 25°C <sup>(1)</sup>	-2.2	Α
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	-8.8	Α
P <sub>D</sub>	Power Dissipation <sup>(1)</sup>	1.5	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C

- (1)  $R_{\theta JA} = 85^{\circ}\text{C/W}$  on  $1\text{in}^2$  Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Static Cl	Static Characteristics						
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = -250\mu A$	-20			V	
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -16V			-1	μА	
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 8V$			-100	nA	
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.75	-1	V	
		$V_{GS} = -1.5V$ , $I_D = -1A$		175	220	mΩ	
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = -2.5V$ , $I_{D} = -1A$		80	100	mΩ	
		$V_{GS} = -4.5V$ , $I_{D} = -1A$		62	75	mΩ	
g <sub>fs</sub>	Transconductance	$V_{DS} = -10V, I_{D} = -1A$		5.8		S	
Dynamic	Characteristics		·				
C <sub>ISS</sub>	Input Capacitance			210	270	pF	
C <sub>OSS</sub>	Output Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = -10V, f = 1MHz		90	120	pF	
C <sub>RSS</sub>	Reverse Transfer Capacitance			30	40	pF	
Qg	Gate Charge Total (-4.5V)			1.9	2.5	nC	
$Q_{gd}$	Gate Charge Gate to Drain	V 40V I 4A		0.4		nC	
Q <sub>gs</sub>	Gate Charge Gate to Source	$V_{DS} = -10V, I_{D} = -1A$ 0.3		0.35		nC	
Qg(th)	Gate Charge at Vth			0.17		nC	
Q <sub>OSS</sub>	Output Charge	$V_{DS} = -9.8V, V_{GS} = 0V$		1.7		nC	
t <sub>d(on)</sub>	Turn On Delay Time			4		ns	
t <sub>r</sub>	Rise Time	$V_{DS} = -10V$ , $V_{GS} = -4.5V$ , $I_{D} = -1A$		2		ns	
t <sub>d(off)</sub>	Turn Off Delay Time	$R_G = 20\Omega$		29		ns	
t <sub>f</sub>	Fall Time			12		ns	
Diode C	haracteristics		<u>.                                    </u>		,		
V <sub>SD</sub>	Diode Forward Voltage	$I_S = -1A$ , $V_{GS} = 0V$		-0.75	-1	V	
$Q_{rr}$	Reverse Recovery Charge	$V_{dd} = -9.8V$ , $I_F = -1A$ , $di/dt = 200A/\mu s$		0.9		nC	
t <sub>rr</sub>	Reverse Recovery Time	$V_{dd} = -9.8V$ , $I_F = -1A$ , $di/dt = 200A/\mu s$		8.2		ns	

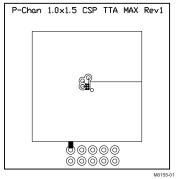
## THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

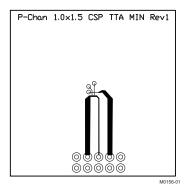
PARAMETER		MIN	TYP	MAX	UNIT
R $_{\theta JC}$	Thermal Resistance Junction to Ambient (Minimum Cu area)			270	°C/W
R $_{\theta JA}$	Thermal Resistance Junction to Ambient (1 in <sup>2</sup> Cu area)			105	°C/W



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Max  $R_{\theta JA} = 105$ °C/W when mounted on 1 inch<sup>2</sup> of 2 oz. Cu.



Max  $R_{\theta JA} = 270^{\circ} C/W$  when mounted on minimum pad area of 2 oz. Cu.

#### TYPICAL MOSFET CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

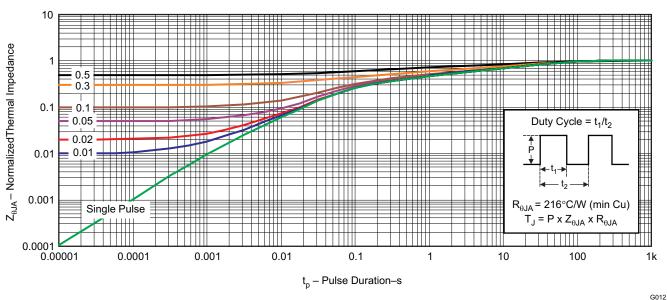


Figure 1. Transient Thermal Impedance

# TEXAS INSTRUMENTS

## TYPICAL MOSFET CHARACTERISTICS (continued)

(T<sub>A</sub> = 25°C unless otherwise stated)

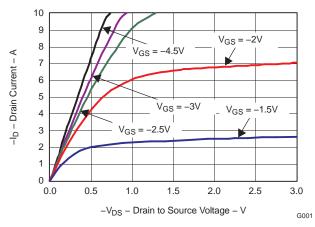


Figure 2. Saturation Characteristics

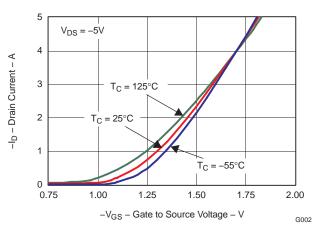


Figure 3. Transfer Characteristics

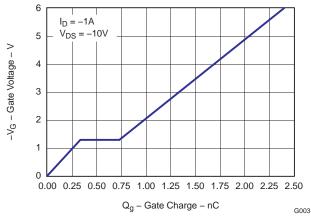


Figure 4. Gate Charge

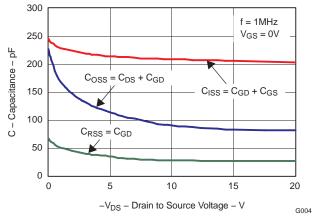


Figure 5. Capacitance

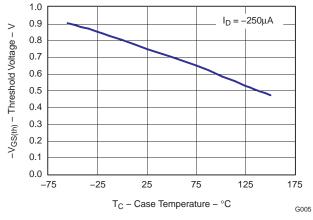


Figure 6. Threshold Voltage vs. Temperature

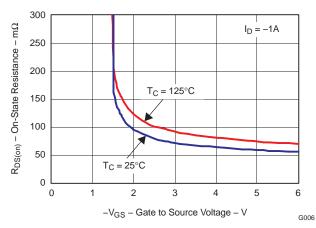


Figure 7. On Resistance vs. Gate Voltage

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## TYPICAL MOSFET CHARACTERISTICS (continued)

(T<sub>A</sub> = 25°C unless otherwise stated)

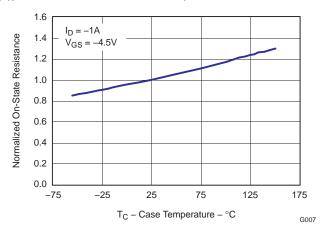


Figure 8. On Resistance vs. Temperature

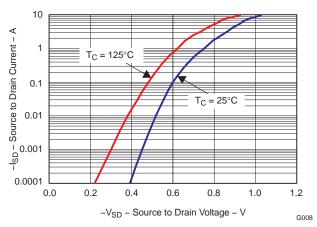


Figure 9. Typical Diode Forward Voltage

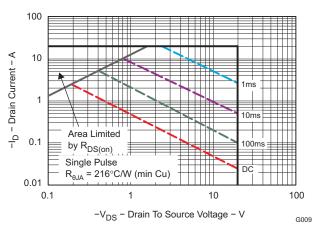


Figure 10. Maximum Safe Operating Area

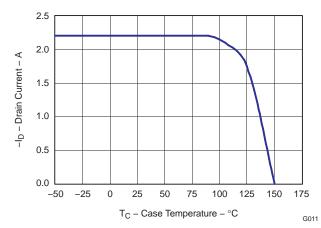
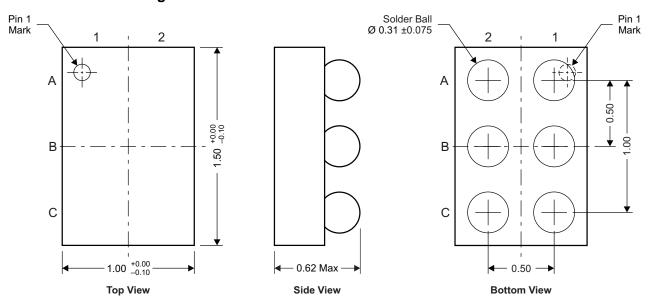


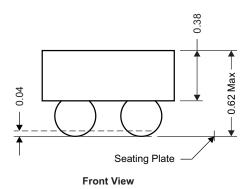
Figure 11. Maximum Drain Current vs. Temperature



## **MECHANICAL DATA**

## CSD25301W1015 Package Dimensions





M0157-01

NOTE: All dimensions are in mm (unless otherwise specified)

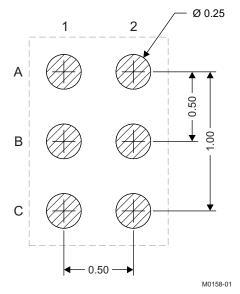
## **Pinout**

POSITION	DESIGNATION
C1, C2	Drain
A1	Gate
A2, B1, B2	Source



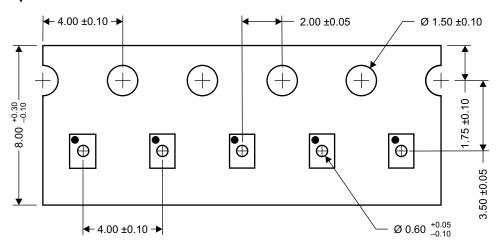
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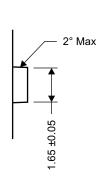
## **Land Pattern Recommendation**

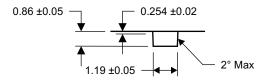


NOTE: All dimensions are in mm (unless otherwise specified)

## **Tape and Reel Information**







NOTE: All dimensions are in mm (unless otherwise specified)

M0159-01



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## **Package Marking Information**

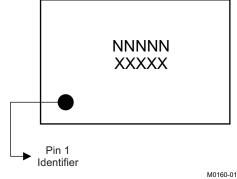
Location

1st Line

= NNNNN, First 5 digits after CSD (Fixed Text) Product Code

2nd Line

XXXXX= Last 5 digits of lot number



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